

BIOFY® Sensor

Version 1.1

SFH 7070



Features:

- Multi chip package featuring two green emitters and one detector
- Package size: (WxDxH) 7.5 mm x 3.9 mm x 0.9 mm
- Light Barriers to block optical crosstalk
- optimized for strong PPG signal

Applications

- Heart rate monitoring

for:

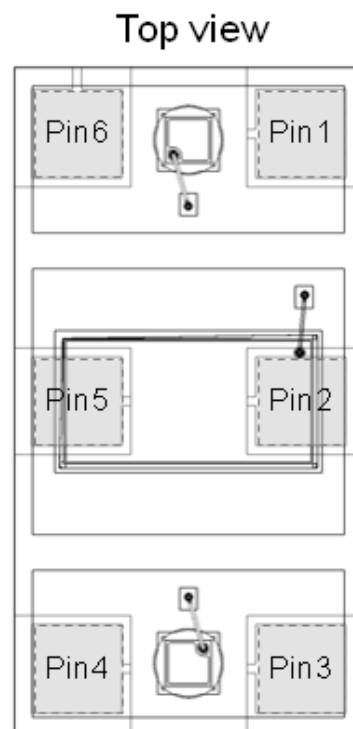
- Wearable devices (e.g. smart watches, fitness trackers, ...)
- Mobile devices

Ordering Information

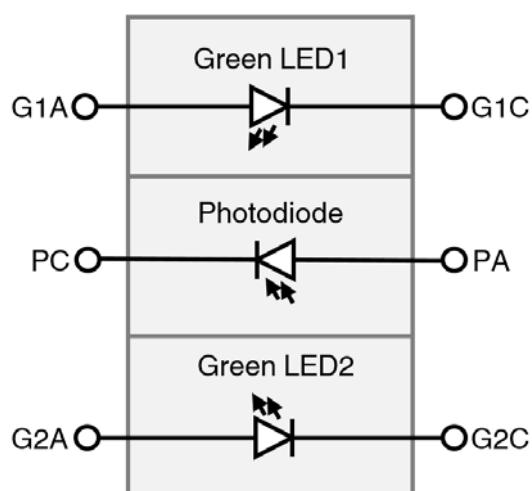
Type	Ordering Code
SFH 7070	Q65111A9887

Pin configuration

Pin	Name	Function
1	G1C	Green LED 1 Cathode
2	PA	Photodiode Anode
3	G2C	Green LED 2 Cathode
4	G2A	Green LED 2 Anode
5	PC	Photodiode Cathode
6	G1A	Green LED 1 Anode



Block diagram



Maximum Ratings ($T_A = 25\text{ °C}$)

Parameter	Symbol	Values	Unit
General			
Operating temperature range	T_{op}	-40 ... 85	°C
Storage temperature range	T_{stg}	-40 ... 85	°C
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V_{ESD}	2	kV
Green Emitters			
Reverse voltage	V_R	5	V
Forward current	$I_F (DC)$	25	mA
Surge current ($t_p = 10\text{ }\mu s$, $D = 0$)	I_{FSM}	300	mA
Detector			
Reverse voltage	V_R	16	V

Characteristics ($T_A = 25\text{ °C}$)

Parameter		Symbol	Value	Unit
Green Emitter (single emitter)				
Wavelength of peak emission ($I_F = 20\text{ mA}$)	(typ.)	λ_{peak}	526	nm
Centroid Wavelength ($I_F = 20\text{ mA}$)	(typ. (max.))	$\lambda_{\text{centroid}}$	530 (± 10)	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 20\text{ mA}$)	(typ.)	$\Delta\lambda$	32	nm
Half angle	(typ.)	φ	± 60	°
Rise and fall time of I_e (10% and 90% of $I_{e\text{ max}}$) ($I_F = 100\text{ mA}$, $t_p = 16\text{ }\mu\text{s}$, $R_L = 50\text{ }\Omega$)	(typ.)	t_r, t_f	56	ns
Forward voltage ($I_F = 20\text{ mA}$)	(typ. (max.))	V_F	3.0 (≤ 3.4)	V
Reverse current ($V_R = 5\text{ V}$)		I_R	not designed for reverse operation	μA
Radiant intensity ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	I_e	3.8	mW / sr
Total radiant flux ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	Φ_e	11.7	mW
Temperature coefficient of I_e or Φ_e ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	TC_I	-0.35	% / K
Temperature coefficient of $\lambda_{\text{centroid}}$ ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	$TC_{\lambda_{\text{centroid}}}$	0.03	nm / K
Temperature coefficient of V_F ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	TC_V	-3.6	mV / K

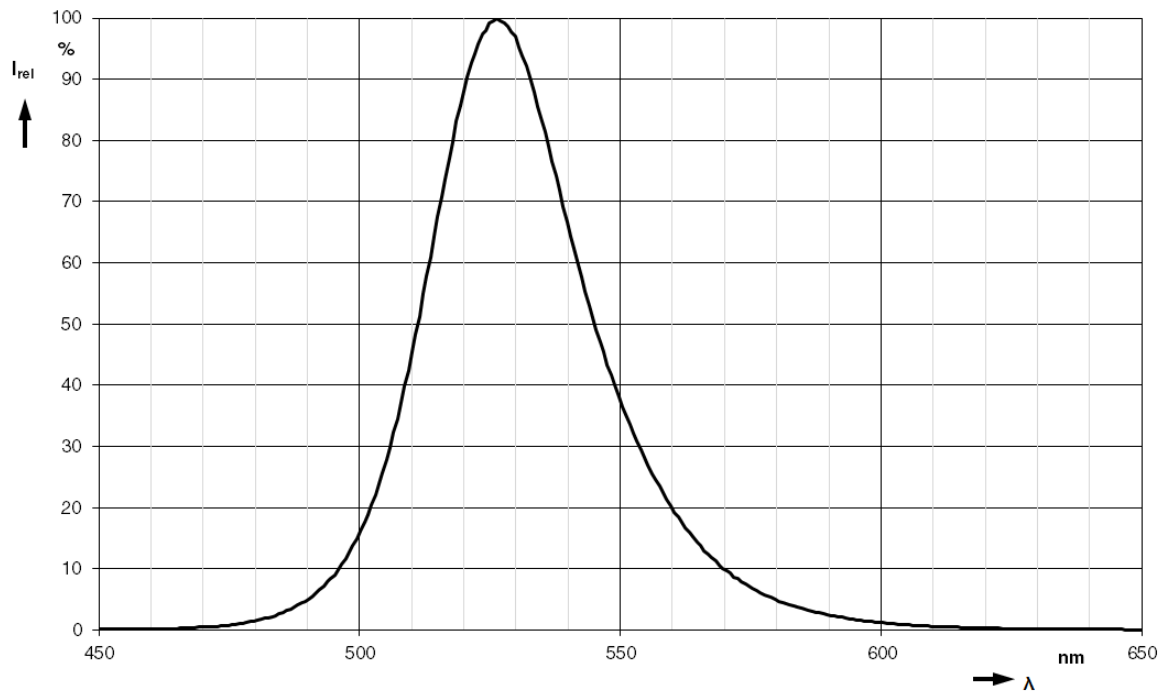
Characteristics ($T_A = 25\text{ °C}$)

Parameter		Symbol	Value	Unit
Detector				
Photocurrent ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 530\text{ nm}$, $V_R = 5\text{ V}$)	(typ.)	$I_{P,530}$	0.985	μA
Wavelength of max. sensitivity	(typ.)	$\lambda_{S\text{ max}}$	635	nm
Spectral range of sensitivity	(typ.)	$\lambda_{10\%}$	402 ... 694	nm
Radiation sensitive area	(typ.)	A	3.46	mm^2
Dimensions of radiant sensitive area	(typ.)	L x W	1.29 x 2.69	mm x mm
Half angle	(typ.)	φ	± 57	°
Dark current ($V_R = 5\text{ V}$, $E_e = 0\text{ mW/cm}^2$)	(typ. (max.))	I_R	0.4 (≤ 5)	nA
Spectral sensitivity of the chip ($\lambda = 530\text{ nm}$)	(typ.)	$S_{\lambda 530}$	0.31	A / W
Spectral sensitivity of the chip ($\lambda > 690\text{ nm}$)	(typ.)	S_{IR}	0.02	A / W
Open-circuit voltage ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 530\text{ nm}$)	(typ.)	$V_{O,535}$	390	mV
Short-circuit current ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 530\text{ nm}$)	(typ.)	$I_{SC,535}$	0.984	μA
Rise and fall time ($V_R = 5\text{ V}$, $R_L = 50\text{ }\Omega$, $\lambda = 530\text{ nm}$)	(typ.)	t_r, t_f	40	ns
Forward voltage ($I_F = 10\text{ mA}$, $E = 0\text{ mW/cm}^2$)	(typ.)	V_F	0.84	V
Capacitance ($V_R = 5\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$)	(typ.)	C_0	55	pF

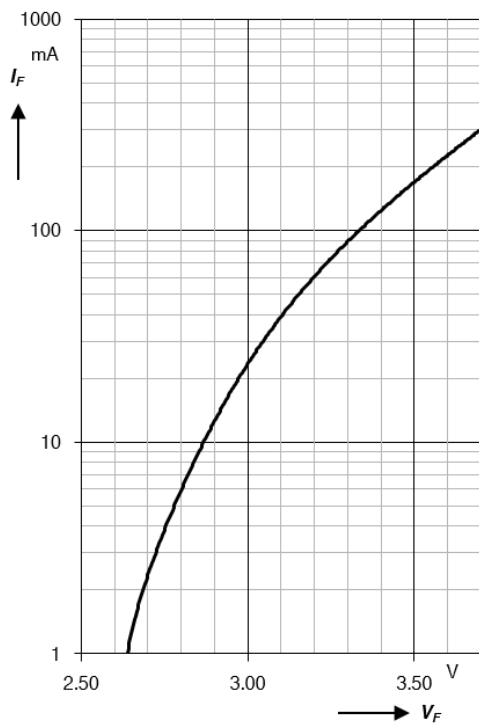
Diagrams for green emitters

Relative spectral emission ¹⁾

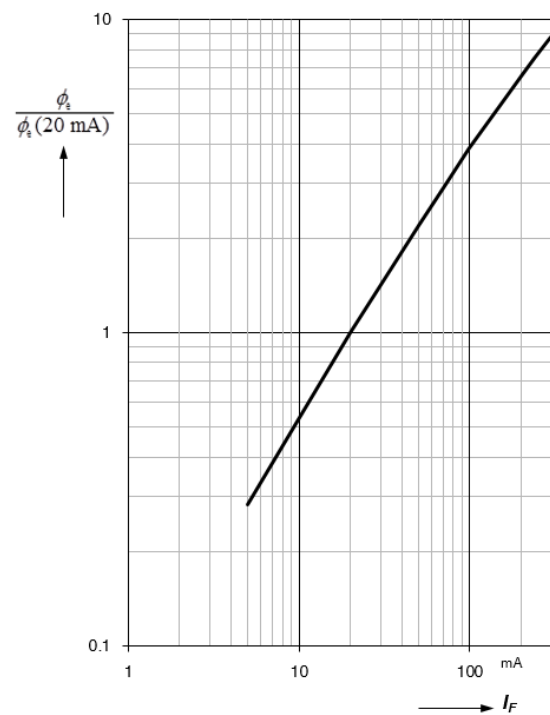
$$I_{\text{rel}} = f(\lambda), T_A = 25^\circ\text{C}, I_F = 20\text{ mA}$$

Forward current ¹⁾

$$I_F = f(V_F), T_A = 25^\circ\text{C}$$

Relative radiant flux ¹⁾

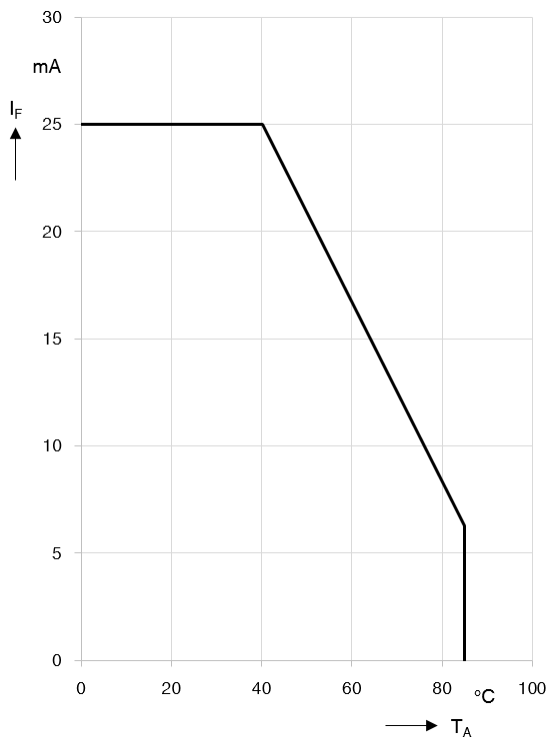
$$\Phi_e / \Phi_e(20\text{ mA}) = f(I_F), \text{ single pulse, } t_p = 25\mu\text{s}, T_A = 25^\circ\text{C}$$



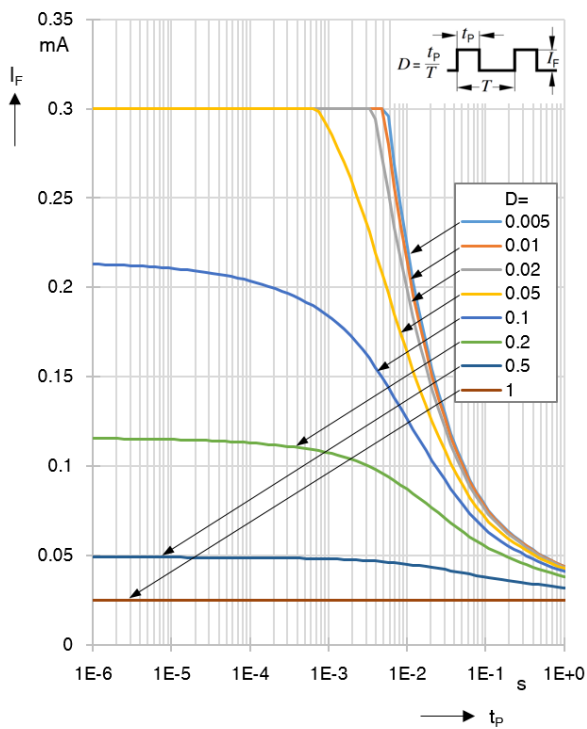
Diagrams for green emitters

Max. permissible forward current ¹⁾

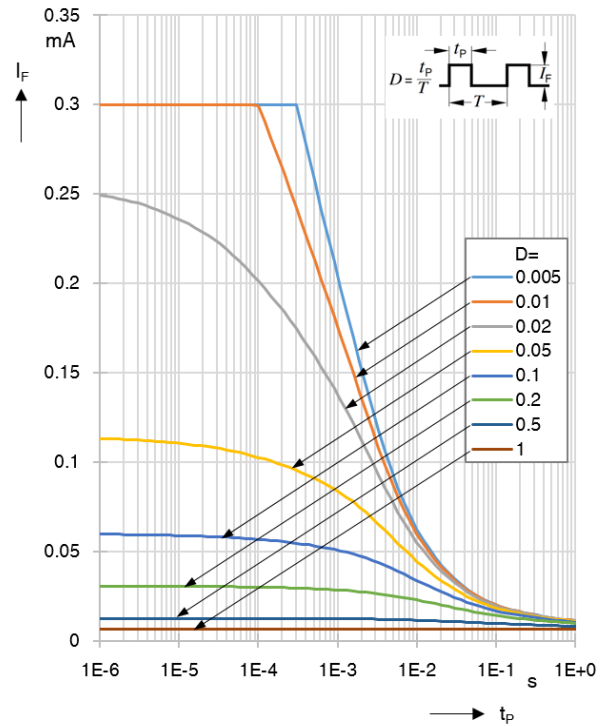
$$I_{F,max} = f(T_A), R_{thJA} = 800 \text{ K/W}$$

Permissible pulse handling capability ¹⁾

$$I_F = f(t_p), T_A = 40^\circ\text{C}, \text{ duty cycle } D$$

Permissible pulse handling capability ¹⁾

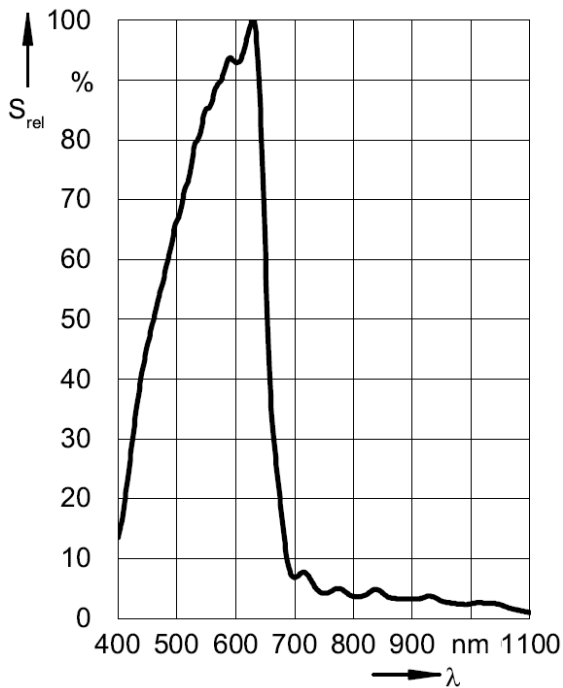
$$I_F = f(t_p), T_A = 85^\circ\text{C}, \text{ duty cycle } D$$



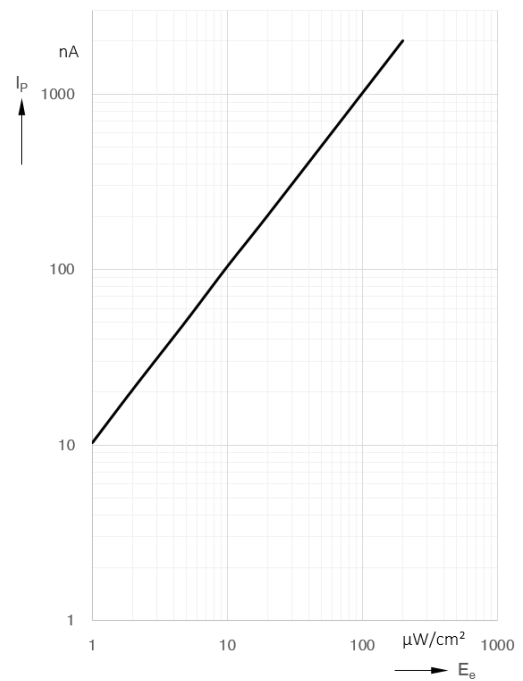
Diagrams for detector

Relative spectral sensitivity ¹⁾

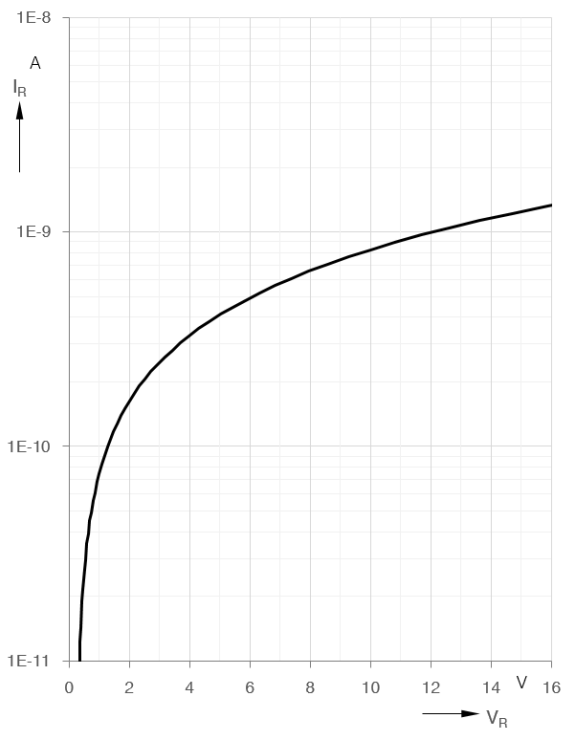
$$S_{\text{rel}} = f(\lambda), T_A = 25^\circ\text{C}$$

Photocurrent ¹⁾

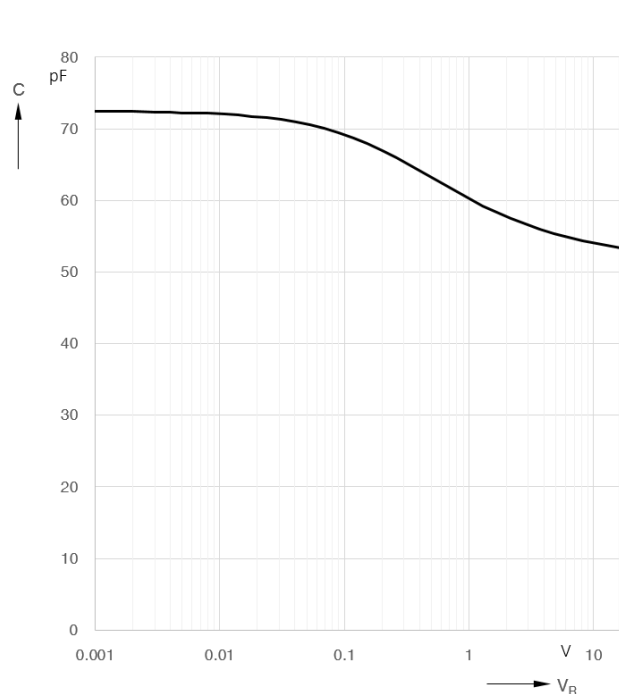
$$I_P(V_R = 5\text{ V}), \lambda = 530\text{ nm}, T_A = 25^\circ\text{C}$$

Dark current ¹⁾

$$I_R = f(V_R), E = 0\text{ mW}/\text{cm}^2, T_A = 25^\circ\text{C}$$

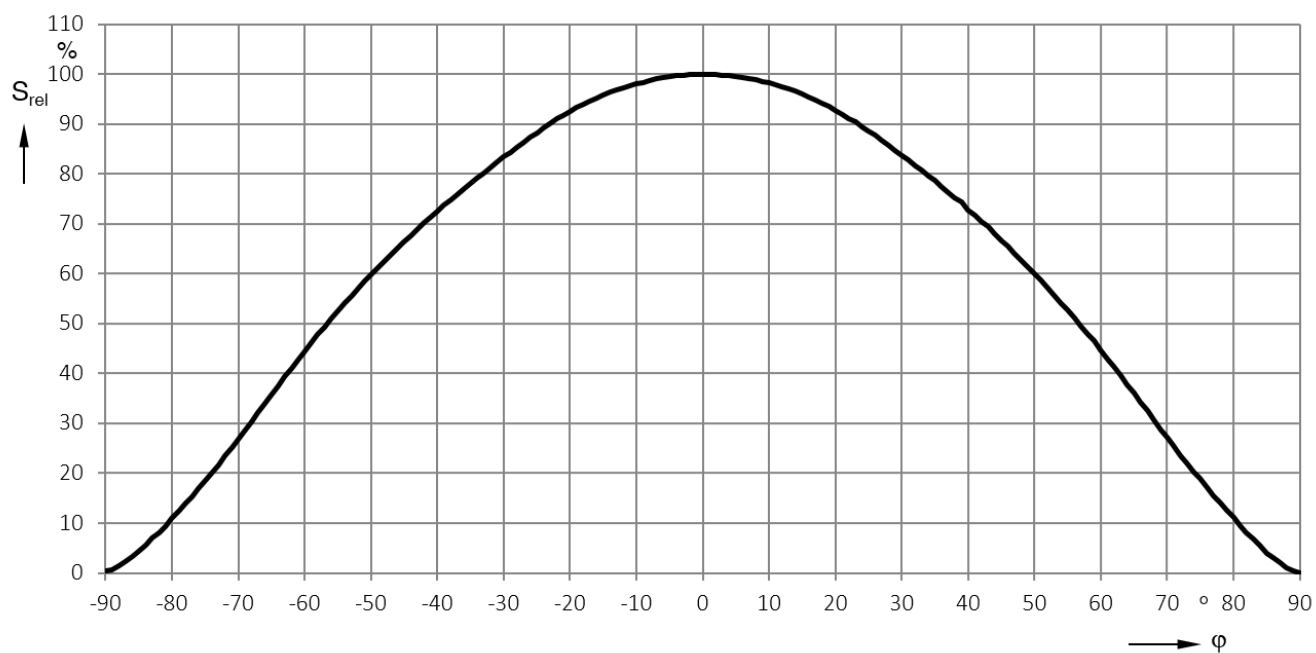
Capacitance ¹⁾

$$C = f(V_R), f = 1\text{ MHz}, E = 0\text{ mW}/\text{cm}^2, T_A = 25^\circ\text{C}$$

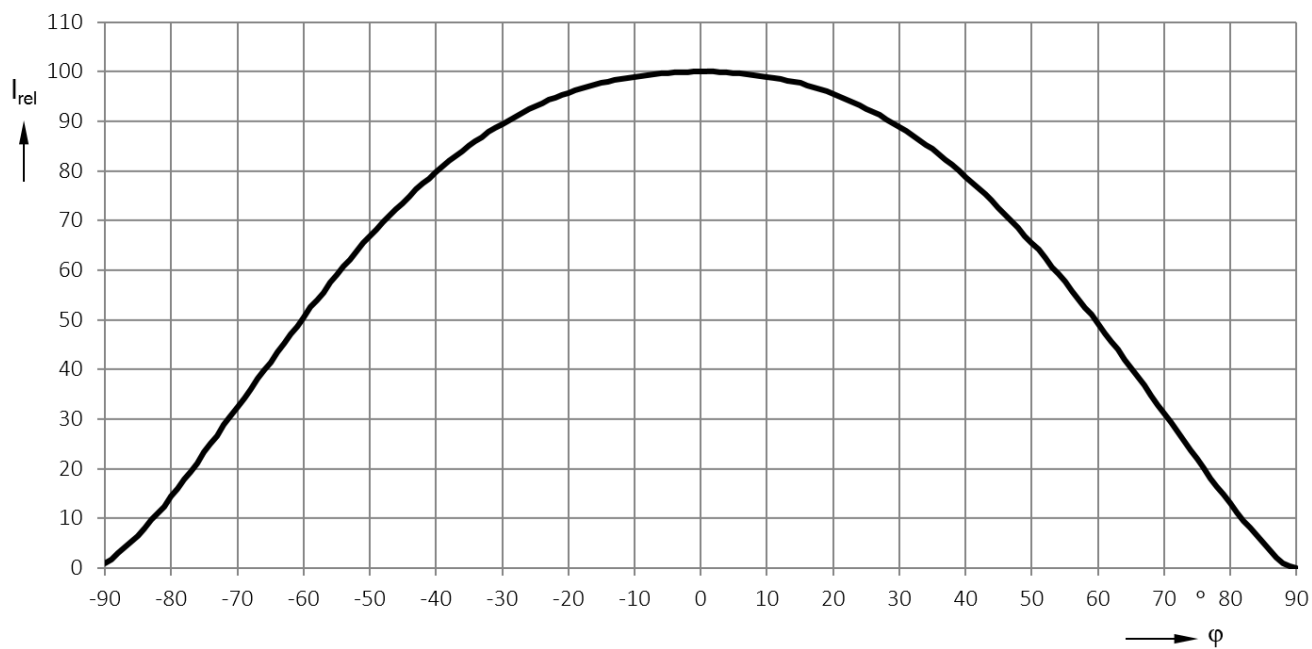


Directional characteristics of detector ¹⁾

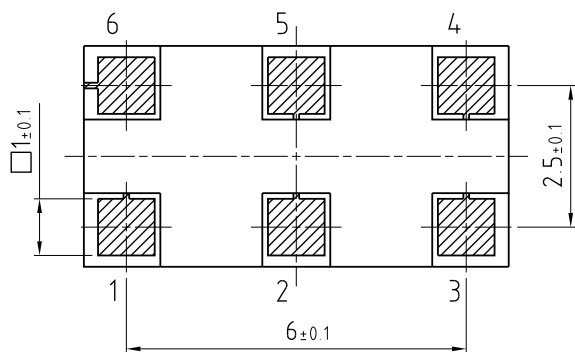
$$S_{\text{rel}} = f(\varphi), \lambda = 530\text{nm}$$

**Radiation characteristics of emitter ¹⁾**

$$I_{\text{rel}} = f(\varphi)$$

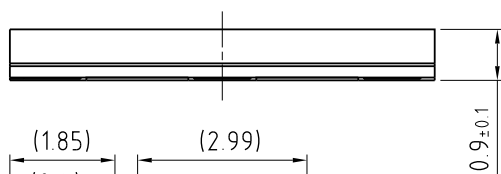


Package Outline

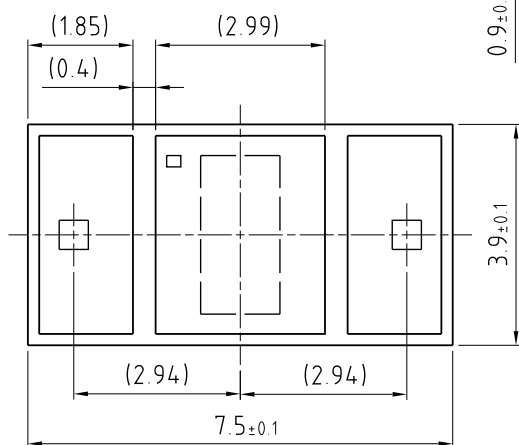


BOTTOM VIEW

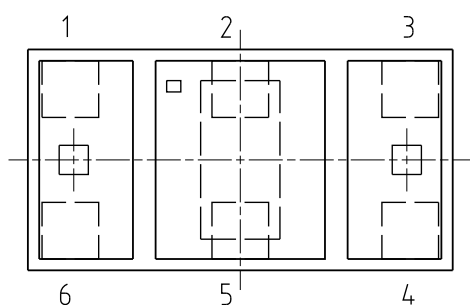
Pin	Name	Function
1	G1C	Green LED1 cathode
2	PA	Photodiode anode
3	G2C	Green LED2 cathode
4	G2A	Green LED2 anode
5	PC	Photodiode cathode
6	G1A	Green LED1 anode



SIDE VIEW



TOP VIEW

TOP VIEW /
Pad Info

C63062-A4310-A1-02

Dimensions in mm

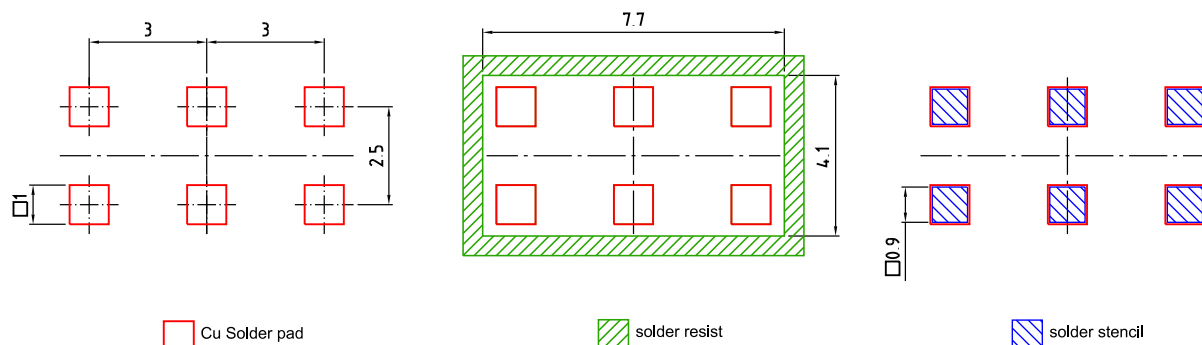
Package:

chip on board

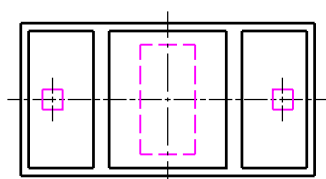
Approximate Weight:

43 mg

Recommended solder pad design



Component Location on Pad

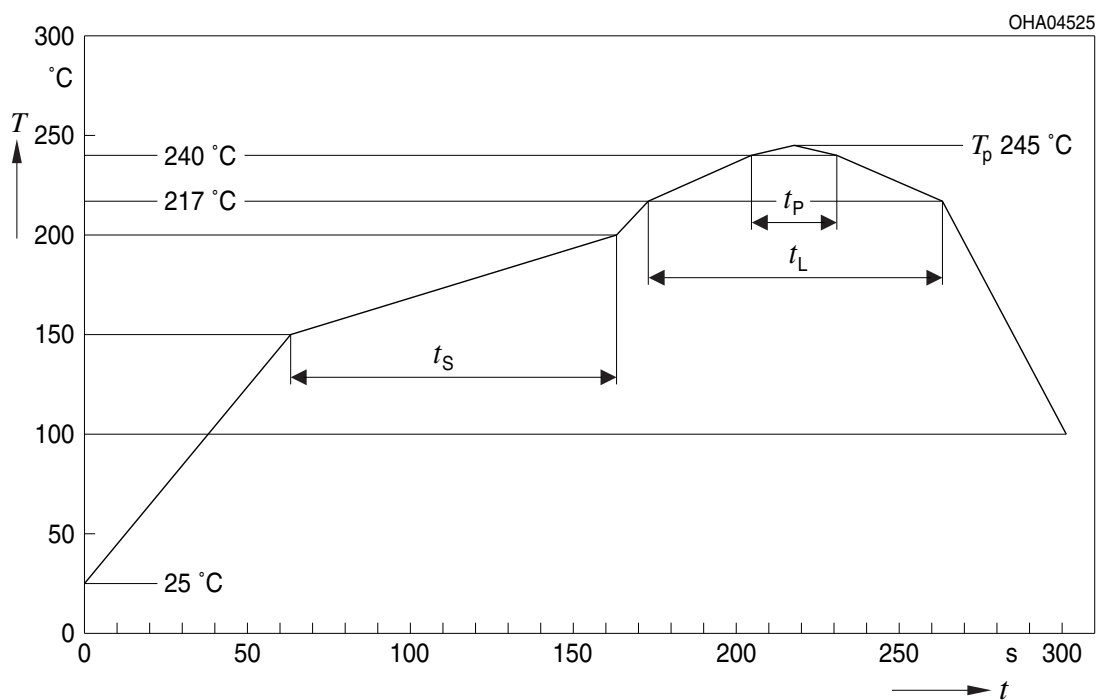


Dimensions in mm (inch).

E062.3010.204-02

Reflow Soldering Profile

Product complies to MSL Level 4 acc. to JEDEC J-STD-020D.01



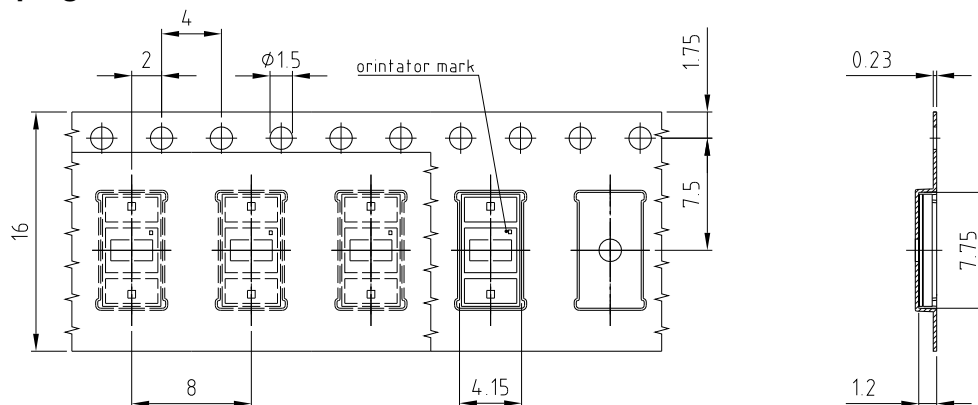
OHA04612

Profile Feature Profil-Charakteristik	Symbol Symbol	Pb-Free (SnAgCu) Assembly			Unit Einheit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*) 25 °C to 150 °C			2	3	K/s
Time t_S T_{Smin} to T_{Smax}	t_S	60	100	120	s
Ramp-up rate to peak*) T_{Smax} to T_P			2	3	K/s
Liquidus temperature	T_L	217			°C
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_P		245	260	°C
Time within 5 °C of the specified peak temperature T_P - 5 K	t_P	10	20	30	s
Ramp-down rate* T_P to 100 °C			3	6	K/s
Time 25 °C to T_P				480	s

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

Method of Taping

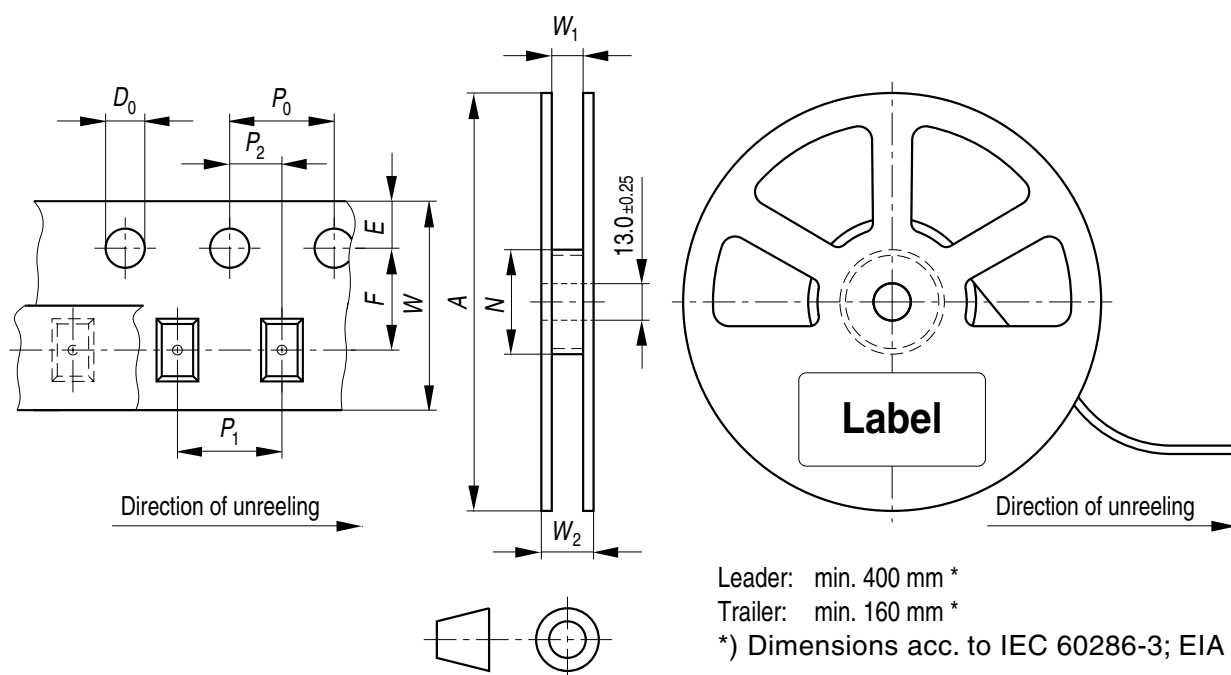


C63062-A4310-B2 -02

Dimensions in mm [inch].

Tape and Reel

16 mm tape with 1500 pcs. on Ø 180 mm reel



Dimensions in mm

Tape Dimensions [mm]

W	P ₀	P ₁	P ₂	D ₀	E	F
16 +0.3 / -0.1	4 ±0.1	8 ±0.1	2 ±0.05	1.5 ±0.1	1.75 ±0.1	7.5 ±0.05

Reel Dimensions [mm]

A	W	N _{min}	W ₁	W _{2max}
180	16	60	16.4 +2	22.4

Barcode-Product-Label (BPL)

OSRAM Opto Semiconductors

LX XXXX BIN1: XX-XX-X-XXX-X

RoHS Compliant

(6P) BATCH NO: 1234567890

(1T) LOT NO: 1234567890 (9D) D/C: 1234

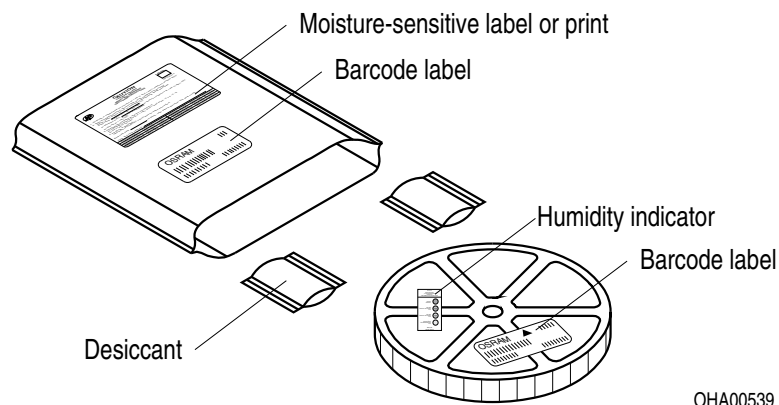
(X) PROD NO: 123456789 (Q) QTY: 9999 (G) GROUP: XX-XX-X-X

ML Temp ST
X XXX °C X

Pack: RXX
DEMY XXX
X_X123_1234.1234 X

OHA04563

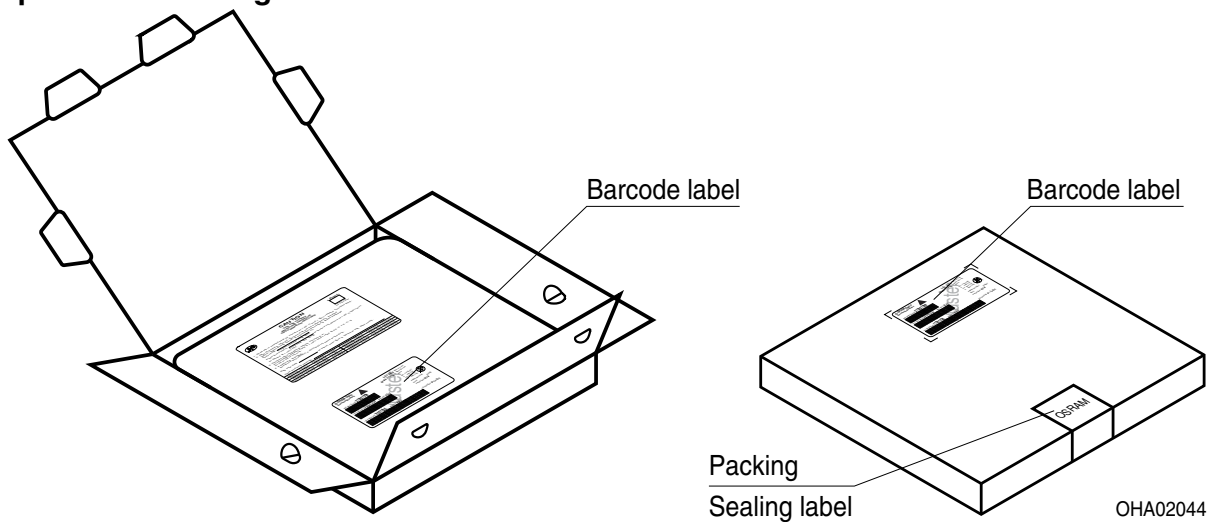
Dry Packing Process and Materials



Note:

Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card. Regarding dry pack you will find further information in the internet. Here you will also find the normative references like JEDEC.

Transportation Packing and Materials



Dimensions of transportation box in mm

Width	Length	Height
195 ± 5	195 ± 5	42 ± 5

Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization. If printed or downloaded, please find the latest version in the Internet.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose!

Critical components* may only be used in life-support devices** or systems with the express written approval of OSRAM OS.

*) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.

**) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.

Glossary

- 1) **Typical Values:** Due to the special conditions of the manufacturing processes of LED and photodiodes, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.

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EU RoHS and China RoHS compliant product



此产品符合欧盟 RoHS 指令的要求；

按照中国的相关法规和标准，不含有毒有害物质或元素。

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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